

APPENDIX A
"Clean" Version of Each Paragraph/Section/Claim
37 C.F.R. § 1.121(b)(ii) and (c)(i)

SPECIFICATION:

New section beginning at page 1, line 2 (after the title):

CROSS REFERENCE TO RELATED APPLICATIONS

AA1
This is a divisional of U.S. Patent Application Serial No. 09/184,218, filed November 2, 1998 in the name of Hideki Fukano and entitled SEMICONDUCTOR PHOTO-DETECTOR, SEMICONDUCTOR PHOTODETECTION DEVICE, AND PRODUCTION METHODS THEREOF.

CLAIMS:

AA2
subcl
7. (Amended) The semiconductor photo-detector as claimed in claim 4, wherein a compositionally graded or step-graded layer from the same composition as said photo-absorption layer to the same composition as said semiconductor layer of large schottky-barrier height is disposed between said photo-absorption layer and said semiconductor layer of large schottky-barrier height.

AA3
subcl
16. (NEW) The semiconductor photo-detector as claimed in claim 5, wherein a compositionally graded or step-graded layer from the same composition as said photo-absorption layer to the same composition as said semiconductor layer of large schottky-barrier height is disposed between said photo-absorption layer and said semiconductor layer of large schottky-barrier height.

17. (NEW) The semiconductor photo-detector as claimed in claim 6, wherein a compositionally graded or step-graded layer from the same composition as said photo-absorption layer to the same composition as said semiconductor layer of large schottky-barrier height is disposed between said photo-absorption layer and said semiconductor layer of large schottky-barrier height.